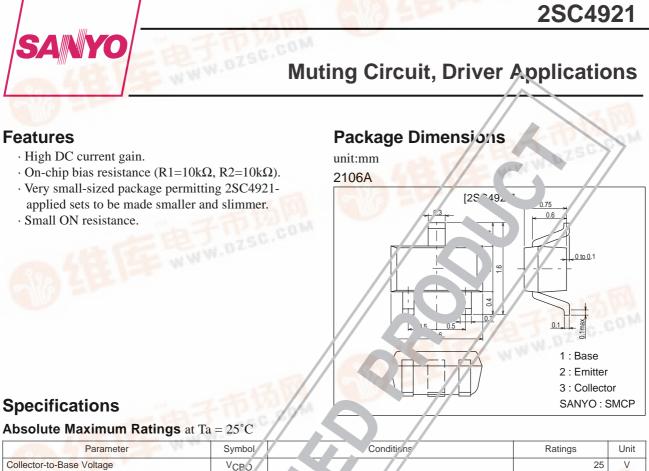
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Ordering number:EN4767

NPN Epitaxial Planar Silicon Transistor



Specifications

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		25	V
Collector-to-Emitter Voltage	VCEO		20	V
Emitter-to-Base Voltage	VF_BO		10	V
Input Voltage	VIN		-18	V
Collector Current	IC		100	mA
Collector Current (Pulse)	6.0		200	mA
Base Current	'B		20	mA
Collector Dissipation	PC		150	mW
Junction Temperature			150	°C
Storage Temperature	Tstg	1	-55 to +150	°C

Electrical Characteristics at Ta 25 C

Parameter	Symbol	Conditions		Unit			
	Symbol		min	typ	max	Unit	
Collector Cutoff Current	ICFO	V _{CB} =20V, I _E =0			1-5-	0.1	μA
	I JE J	V _{CE} =15V, I _B =0		10-	- 1.1	0.5	μA
Emitter Cutoff Cutrent	Ir_BO	V _{EB} =5V, I _C =0		195	250	360	μΑ
DC Current Gain	h _{FE}	V _{CE} =2V, I _C =10mA		100			
Gain-Bandwidth Product	f _T *	V _{CE} =5V, I _C =10mA	and the second sec		240		MHz
Output Cr.pa citance	Cob*	V _{CB} =10V, f=1MHz			1.4		pF
Characteristic of the transis	tor						

Marking . FA

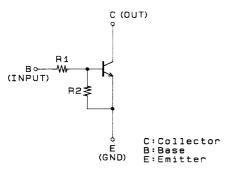
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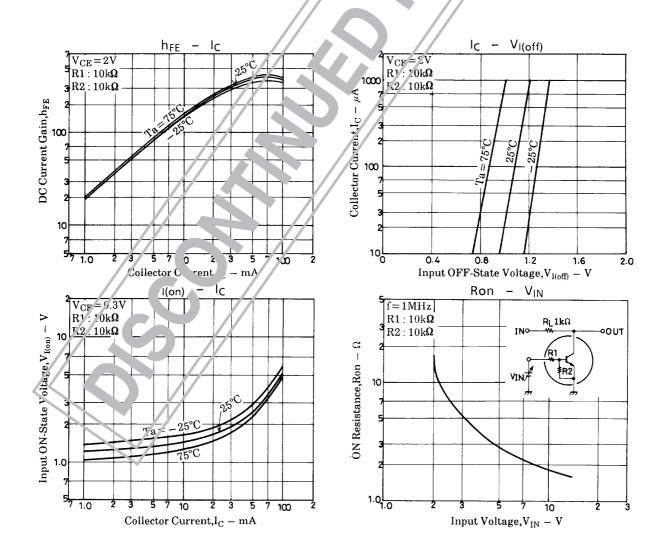
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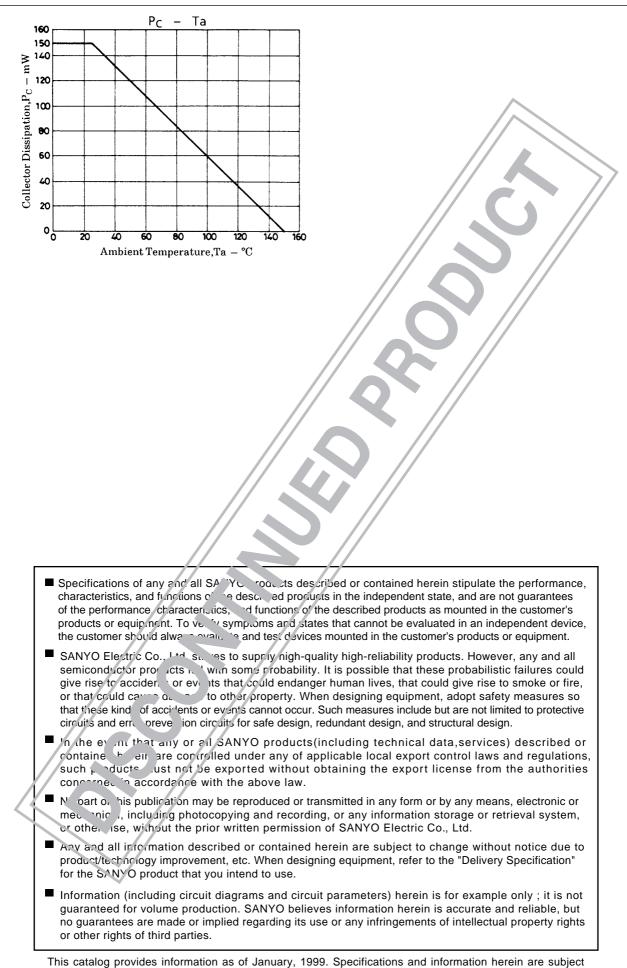
2SC4921

Parameter	Symbol	Conditions		Unit		
	Symbol	Conditions		typ	max	
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =2.5mA, I _B =0.25mA		10	30	mV
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =10µA, I _E =0	25			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	20			V
Input OFF-State Voltage	V _{I(off)}	V _{CE} =2V, I _C =100µA	0.7	1.1	1.4	V
Input ON-State Voltage	V _{I(on)}	V _{CE} =0.3V, I _C =10mA	1.0	1.5	3.0	V
Input Resistance	R1		7.0	10	13	kΩ
Resistance Ratio	R1/R2		0.9	1.0	1.1	
ON Resistance	Ron	V _{IN} =5V, f=1MHz		2.8		Ω

Electrical Connection







to change without notice.